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Title	Method for making deep contact of memory		

Patent Abstract

A method for making a deep contact of memory essentially comprises increasing the silicon concentration at the TiSi_2 interface by vertical implantation and reducing interface thickness, wherein a physical or chemical vapor deposition process is used to deposit titanium, and then silicon ions are vertically implanted, thereby increasing the deposition concentration of Si and effectively removing residues of excessive oxide and polymer to increase the conductivity of contact and the coverage of silicide.